

**This Page Is Inserted by IFW Operations  
and is not a part of the Official Record**

## **BEST AVAILABLE IMAGES**

**Defective images within this document are accurate representations of the original documents submitted by the applicant.**

**Defects in the images may include (but are not limited to):**

- **BLACK BORDERS**
- **TEXT CUT OFF AT TOP, BOTTOM OR SIDES**
- **FADED TEXT**
- **ILLEGIBLE TEXT**
- **SKEWED/SLANTED IMAGES**
- **COLORED PHOTOS**
- **BLACK OR VERY BLACK AND WHITE DARK PHOTOS**
- **GRAY SCALE DOCUMENTS**

**IMAGES ARE BEST AVAILABLE COPY.**

**As rescanning documents *will not* correct images,  
please do not report the images to the  
Image Problem Mailbox.**

**WEST**[Help](#)[Logout](#)[Interrupt](#)

09/652,619

[Main Menu](#)[Search Form](#)[Posting Counts](#)[Show S Numbers](#)[Edit S Numbers](#)[Preferences](#)[Cases](#)**Search Results -**

Terms	Documents
L5 and germanium	2

**Database:**

US Patents Full-Text Database  
US Pre-Grant Publication Full-Text Database  
JPO Abstracts Database  
EPO Abstracts Database  
Derwent World Patents Index  
IBM Technical Disclosure Bulletins

**Search:**

L6

[Refine Search](#)[Recall Text](#)[Clear](#)**Search History****DATE:** Monday, April 08, 2002   [Printable Copy](#)   [Create Case](#)**Set Name Query**

side by side

**Hit Count Set Name**

result set

*DB=USPT; PLUR=YES; OP=OR*

<u>L6</u>	L5 and germanium	2	<u>L6</u>
<u>L5</u>	L4 and (undoped near polysilicon)	11	<u>L5</u>
<u>L4</u>	L3 and lining	162	<u>L4</u>
<u>L3</u>	L2 and (titanium nitride)	2947	<u>L3</u>
<u>L2</u>	L1 and bpsg	3519	<u>L2</u>
<u>L1</u>	integrated near circuit	167942	<u>L1</u>

END OF SEARCH HISTORY

**WEST**[Generate Collection](#)[Print](#)**Search Results - Record(s) 1 through 2 of 2 returned.**☐ 1. Document ID: US 6261964 B1

L6: Entry 1 of 2

File: USPT

Jul 17, 2001

US-PAT-NO: 6261964

DOCUMENT-IDENTIFIER: US 6261964 B1

TITLE: Material removal method for forming a structure

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	RWC
Draw	Desc	Image									

☐ 2. Document ID: US 6232196 B1

L6: Entry 2 of 2

File: USPT,

May 15, 2001

US-PAT-NO: 6232196

DOCUMENT-IDENTIFIER: US 6232196 B1

TITLE: Method of depositing silicon with high step coverage

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	RWC
Draw	Desc	Image									

[Generate Collection](#)[Print](#)

Terms	Documents
L5 and germanium	2

**Display Format:**

TI

[Change Format](#)[Previous Page](#)[Next Page](#)

**WEST**[Generate Collection](#)[Print](#)**Search Results - Record(s) 1 through 10 of 11 returned.**☐ 1. Document ID: US 6358793 B1

L5: Entry 1 of 11

File: USPT

Mar 19, 2002

US-PAT-NO: 6358793

DOCUMENT-IDENTIFIER: US 6358793 B1

TITLE: Method for localized masking for semiconductor structure development

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

[KIMC](#)☐ 2. Document ID: US 6310375 B1

L5: Entry 2 of 11

File: USPT

Oct 30, 2001

US-PAT-NO: 6310375

DOCUMENT-IDENTIFIER: US 6310375 B1

TITLE: Trench capacitor with isolation collar and corresponding manufacturing method

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

[KIMC](#)☐ 3. Document ID: US 6309975 B1

L5: Entry 3 of 11

File: USPT

Oct 30, 2001

US-PAT-NO: 6309975

DOCUMENT-IDENTIFIER: US 6309975 B1

TITLE: Methods of making implanted structures

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

[KIMC](#)☐ 4. Document ID: US 6261964 B1

L5: Entry 4 of 11

File: USPT

Jul 17, 2001

US-PAT-NO: 6261964  
DOCUMENT-IDENTIFIER: US 6261964 B1

TITLE: Material removal method for forming a structure

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KWIC

☐ 5. Document ID: US 6232196 B1

L5: Entry 5 of 11

File: USPT

May 15, 2001

US-PAT-NO: 6232196  
DOCUMENT-IDENTIFIER: US 6232196 B1

TITLE: Method of depositing silicon with high step coverage

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KWIC

☐ 6. Document ID: US 6048763 A

L5: Entry 6 of 11

File: USPT

Apr 11, 2000

US-PAT-NO: 6048763  
DOCUMENT-IDENTIFIER: US 6048763 A

TITLE: Integrated capacitor bottom electrode with etch stop layer

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KWIC

☐ 7. Document ID: US 6012336 A

L5: Entry 7 of 11

File: USPT

Jan 11, 2000

US-PAT-NO: 6012336  
DOCUMENT-IDENTIFIER: US 6012336 A

TITLE: Capacitance pressure sensor

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KWIC

☐ 8. Document ID: US 5940713 A

L5: Entry 8 of 11

File: USPT

Aug 17, 1999

US-PAT-NO: 5940713

DOCUMENT-IDENTIFIER: US 5940713 A

TITLE: Method for constructing multiple container capacitor

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

☐ 9. Document ID: US 5162890 A

L5: Entry 9 of 11

File: USPT

Nov 10, 1992

US-PAT-NO: 5162890

DOCUMENT-IDENTIFIER: US 5162890 A

TITLE: Stacked capacitor with sidewall insulation

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

☐ 10. Document ID: US 5104822 A

L5: Entry 10 of 11

File: USPT

Apr 14, 1992

US-PAT-NO: 5104822

DOCUMENT-IDENTIFIER: US 5104822 A

TITLE: Method for creating self-aligned, non-patterned contact areas and stacked capacitors using the method

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

[Generate Collection](#)[Print](#)

Terms	Documents
L4 and (undoped near polysilicon)	11

[Display Format:](#)[Change Format](#)[Previous Page](#)[Next Page](#)

**WEST**[Generate Collection](#)[Print](#)**Search Results - Record(s) 11 through 11 of 11 returned.**☐ 11. Document ID: US 5075817 A

L5: Entry 11 of 11

File: USPT

Dec 24, 1991

US-PAT-NO: 5075817

DOCUMENT-IDENTIFIER: US 5075817 A

TITLE: Trench capacitor for large scale integrated memory

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw	Desc	Image							

KVMC

[Generate Collection](#)[Print](#)

Terms	Documents
L4 and (undoped near polysilicon)	11

**Display Format:**

TI

[Change Format](#)[Previous Page](#)[Next Page](#)